

AMENDMENTS TO THE CLAIMS

Claims 1-25 (withdrawn).

26. (currently amended) A composition suitable for use in etching an insulative layer formed over a substrate in a semiconductor device, said composition comprising:

a ~~gaseous~~ flowing plasma etchant mixture consisting essentially of at least one fluorocarbon and ammonia, wherein said ammonia has a flow rate that is from about 2 sccm to about 6 sccm.

27. (previously amended) The composition of claim 26, wherein said fluorocarbon is at least one member selected from the group consisting of fluorohydrocarbons, chlorofluorocarbons and chlorofluorohydrocarbons.

28. (original) The composition of claim 27, wherein said fluorocarbon is at least one member selected from the group consisting of  $C_4F_8$ ,  $C_4F_6$ ,  $C_5F_8$ ,  $CF_4$ ,  $C_2F_6$ ,  $C_3F_8$ ,  $CHF_3$ , and  $CH_2F_2$ .

29. (original) The composition of claim 26, wherein said fluorocarbon is at least one member selected from the group consisting of  $CF_4$ ,  $CHF_3$ , and  $CH_2F_2$ .

30. (original) The composition of claim 29, wherein said fluorocarbon is at least two members selected from the group consisting of  $CF_4$ ,  $CHF_3$ , and  $CH_2F_2$ .

31. (original) The composition of claim 30, wherein said fluorocarbon is a combination of  $CF_4$ ,  $CHF_3$ , and  $CH_2F_2$ .

32. (currently amended) The composition of claim 26, wherein said composition ~~does not~~ is ineffective to remove side wall spacers of a gate stack ~~which is also~~ formed over said substrate.

33. (previously amended) The composition of claim 26, wherein the flow rate ratio of said fluorocarbon to said ammonia is not less than about 3:1.

34. (original) The composition of claim 33, wherein said flow rate ratio is within the range of about 3:1 to about 20:1.

35. (previously amended) The composition of claim 34, wherein said flow rate ratio is within the range of about 4:1 to about 10:1.

Claims 36-70 (withdrawn).

71. (currently amended) A composition suitable for use in etching an insulative layer formed on a substrate in a semiconductor device, said composition comprising:

a ~~gaseous~~ flowing plasma etchant mixture consisting of at least one fluorocarbon and ammonia ~~flowed into a reaction chamber, said reaction chamber having~~ under an operating pressure of from about 30 to about 60 milliTorr, wherein the flow rate ratio of said at least one fluorocarbon to said ammonia is from about 2:1 to about 40:1.

72. (currently amended) A composition suitable for use in etching an insulative layer formed on a substrate in a semiconductor device, said composition comprising:

a ~~gaseous~~ flowing plasma etchant mixture consisting of at least one fluorocarbon and ammonia ~~flowed into a reaction chamber~~ under an operating temperature of from about -50°C to about 80°C, wherein said ammonia has a flow rate that is from about 2 sccm to about 6 sccm.

73. (new) The composition of claim 26, wherein said fluorocarbon is  $\text{CF}_4$  with a flow rate of about 15 sccm to about 20 sccm.

74. (new) The composition of claim 26, wherein said fluorocarbon is  $\text{CHF}_3$  with a flow rate of about 35 sccm to about 45 sccm.

75. (new) The composition of claim 26, wherein said fluorocarbon is  $\text{CH}_2\text{F}_2$  with a flow rate of about 10 sccm to about 15 sccm.

76. (new) The composition of claim 26, wherein said fluorocarbon has a flow rate that is from about 10 sccm to about 40 sccm.